

GaAs PHEMT MEDIUM POWER AMPLIFIER, 17 - 24 GHz

Typical Applications

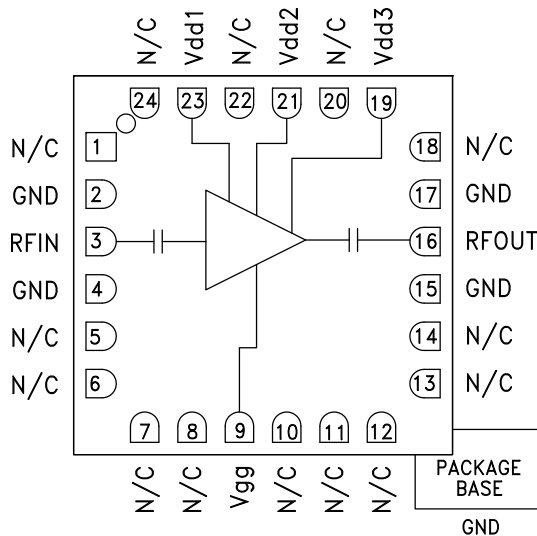
The HMC498LC4 is ideal for use as a LNA or Driver amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment & Sensors
- Military End-Use

Features

- Output IP3: +36 dBm
- Saturated Power: +26 dBm @ 23% PAE
- Gain: 22 dB
- +5V @ 250 mA Supply
- 50 Ohm Matched Input/Output
- RoHS Compliant 4x4 mm SMT Package

Functional Diagram



General Description

The HMC498LC4 is a high dynamic range GaAs PHEMT MMIC Medium Power Amplifier housed in a leadless "Pb free" SMT package. Operating from 17 to 24 GHz, the amplifier provides 22 dB of gain, +26 dBm of saturated power and 23% PAE from a +5V supply voltage. Noise figure is 4 dB while output IP3 is +36 dBm typical enabling the HMC498LC4 to function as a low noise front end as well as a driver amplifier. The RF I/Os are DC blocked and matched to 50 Ohms for ease of use. The HMC498LC4 eliminates the need for wire bonding, allowing use of surface mount manufacturing techniques.

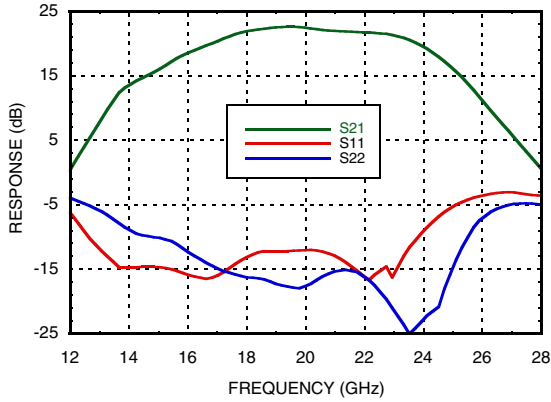
Electrical Specifications, $T_A = +25^\circ C$, $V_{dd1, 2, 3} = 5V$, $I_{dd} = 250 mA^*$

| Parameter | Min. | Typ. | Max. | Min. | Typ. | Max. | Min. | Typ. | Max. | Units |
|--|---------|------|------|---------|------|------|---------|------|------|-------|
| Frequency Range | 17 - 19 | | | 19 - 23 | | | 23 - 24 | | | GHz |
| Gain | 18 | 22 | | 20 | 22.5 | | 18 | 21 | | dB |
| Gain Variation Over Temperature | | 0.02 | 0.03 | | 0.02 | 0.03 | | 0.02 | 0.03 | dB/°C |
| Input Return Loss | | 13 | | | 13 | | | 10 | | dB |
| Output Return Loss | | 15 | | | 15 | | | 20 | | dB |
| Output Power for 1 dB Compression (P1dB) | 22 | 25 | | 21.5 | 24.5 | | 22.5 | 25.5 | | dBm |
| Saturated Output Power (P _{sat}) | | 26.5 | | | 25.5 | | | 26.5 | | dBm |
| Output Third Order Intercept (IP3) | | 35 | | | 36 | | | 35.5 | | dBm |
| Noise Figure | | 4.0 | | | 4.0 | | | 4.5 | | dB |
| Supply Current (I _{dd})(V _{dd} = +5V, V _{gg} = -0.8V Typ.) | | 250 | | | 250 | | | 250 | | mA |

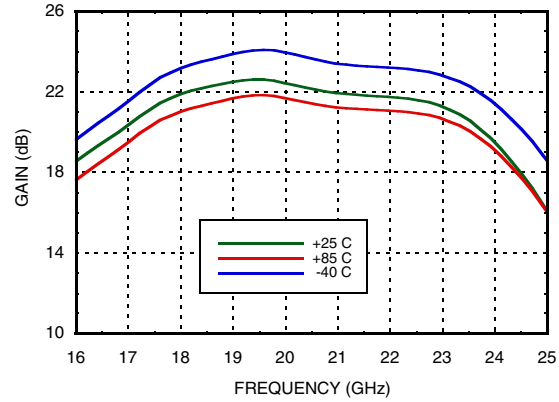
* Adjust V_{gg} between -2 to 0V to achieve I_{dd} = 250 mA typical.

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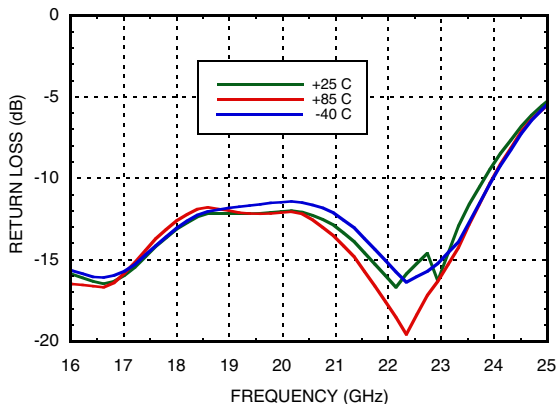
Broadband Gain & Return Loss



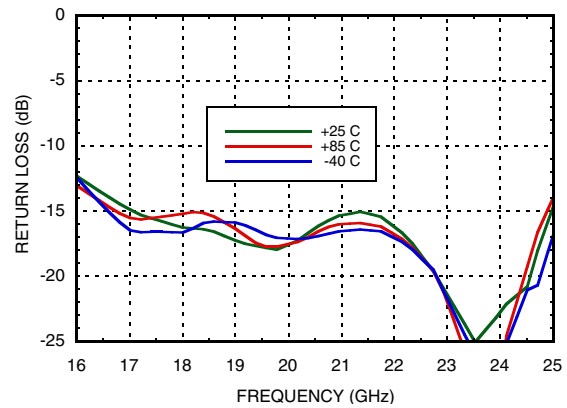
Gain vs. Temperature



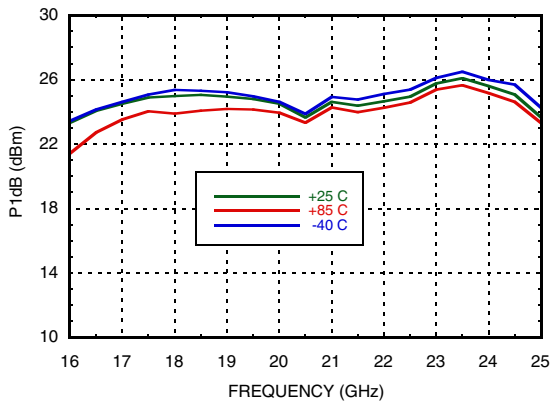
Input Return Loss vs. Temperature



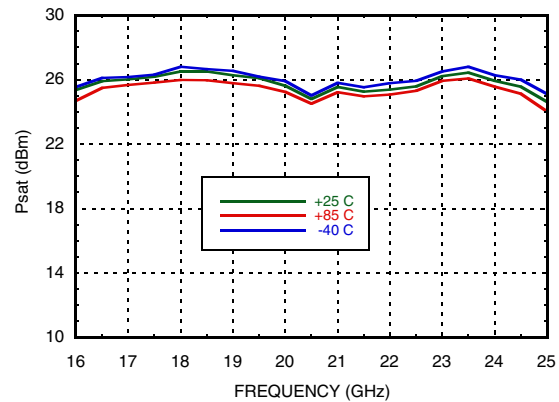
Output Return Loss vs. Temperature



P1dB vs. Temperature

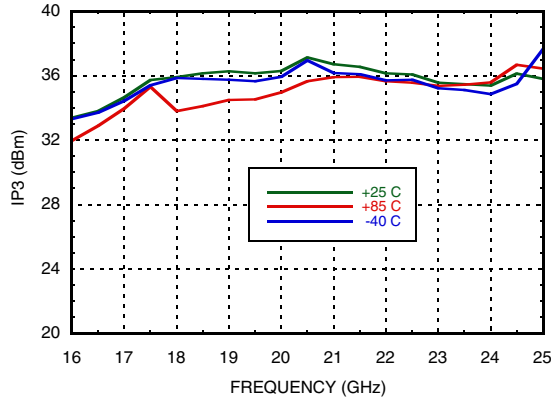


Psat vs. Temperature

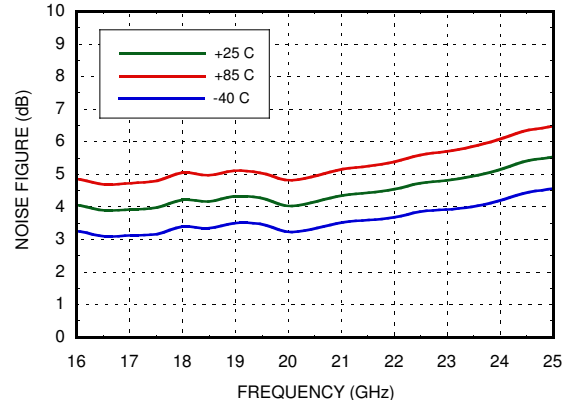


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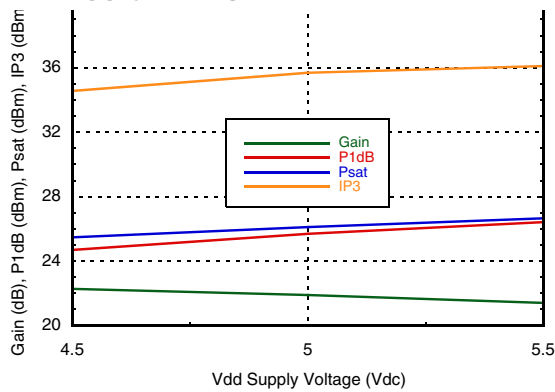
Output IP3 vs. Temperature



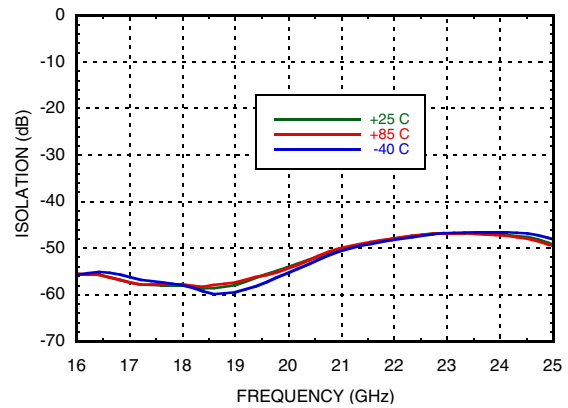
Noise Figure vs. Temperature



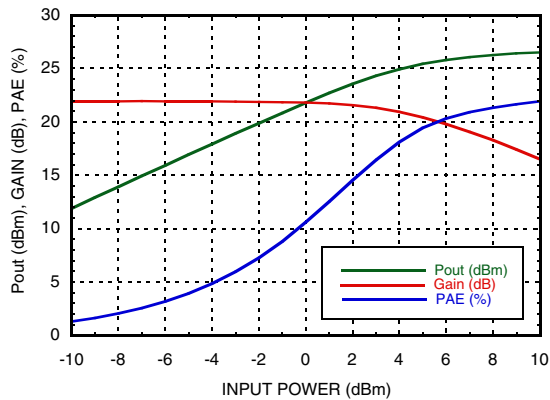
Gain, Power & OIP3 vs. Supply Voltage @ 23 GHz



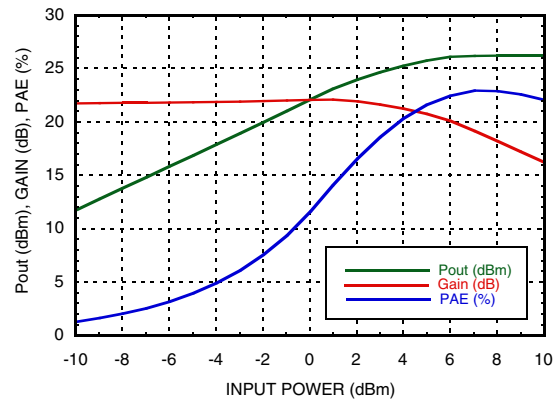
Reverse Isolation vs. Temperature



Power Compression @ 18 GHz



Power Compression @ 23 GHz



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Absolute Maximum Ratings

| | |
|--|----------------|
| Drain Bias Voltage (Vdd1, Vdd2, Vdd3) | +5.5 Vdc |
| Gate Bias Voltage (Vgg) | -4.0 to 0 Vdc |
| RF Input Power (RFIN)(Vdd = +5Vdc) | +10 dBm |
| Channel Temperature | 175 °C |
| Continuous Pdiss (T= 85 °C) (derate 18 mW/°C above 85 °C) | 1.62 W |
| Thermal Resistance (channel to ground paddle) | 55.6 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |
| ESD Sensitivity (HBM) | Class 1A |

Typical Supply Current vs. Vdd

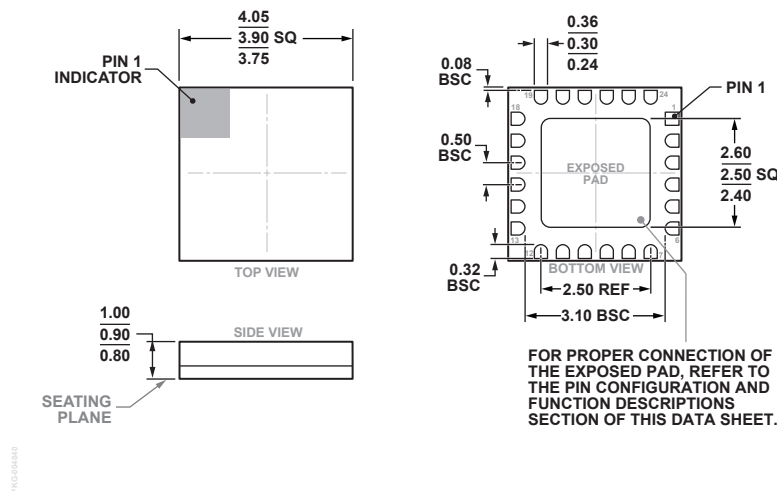
| Vdd (Vdc) | Idd (mA) |
|-----------|----------|
| +4.5 | 239 |
| +5.0 | 250 |
| +5.5 | 262 |

Note: Amplifier will operate over full voltage ranges shown above. Vgg adjusted to achieve Idd= 250 mA at +5V.



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



24-Terminal Ceramic Leadless Chip Carrier [LCC]
(E-24-1)

Dimensions shown in millimeters.

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking [2] |
|-------------|-----------------------|------------------|------------|---------------------|
| HMC498LC4 | Alumina, White | Gold over Nickel | MSL3 [1] | H498 XXXX |

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

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Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|-----------------------------------|------------------|---|---------------------|
| 1, 5 - 8, 10 - 14, 18, 20, 22, 24 | N/C | These pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally. | |
| 2, 4, 15, 17 | GND | Package bottom has an exposed metal paddle that must also be connected to RF/DC ground. | |
| 3 | RFIN | This pin is AC coupled and matched to 50 Ohms. | |
| 9 | Vgg | Gate control for amplifier. Adjust to achieve Id of 250 mA. Please follow "MMIC Amplifier Biasing Procedure" Application Note. External bypass capacitors of 100 pF, 1000 pF and 2.2 μF are required. | |
| 16 | RFOUT | This pin is AC coupled and matched to 50 Ohms. | |
| 23, 21, 19 | Vdd1, Vdd2, Vdd3 | Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1000pF, and 2.2 μF are required. | |

Application Circuit

